/ Revised record

F	2018-4				
G	2018-10-22				
H	2019-1-09	1			
I	2019-6-13		取消 RDSON@-20V/-10A 的项目		
J	2022-1-10		VGSS= ± 20V ± 25V; IGSS VGSS= ± 20V ± 25V E		
A	2022-2-25	ALL	AOS-AOSP21307 BRCS4407SC		

BRCS4407SC

Rev.A Feb.-2022

DATA SHEET

SOP-8 P MOS

P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

V_{DS} (V) = -30V

I_D = -14A (V_{GS} = ± 25v or n

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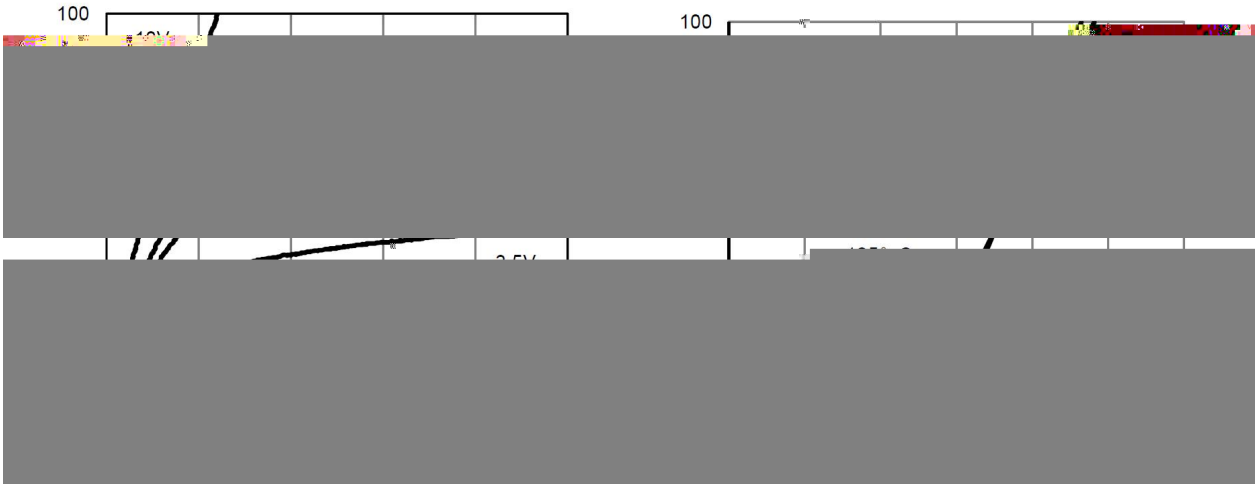
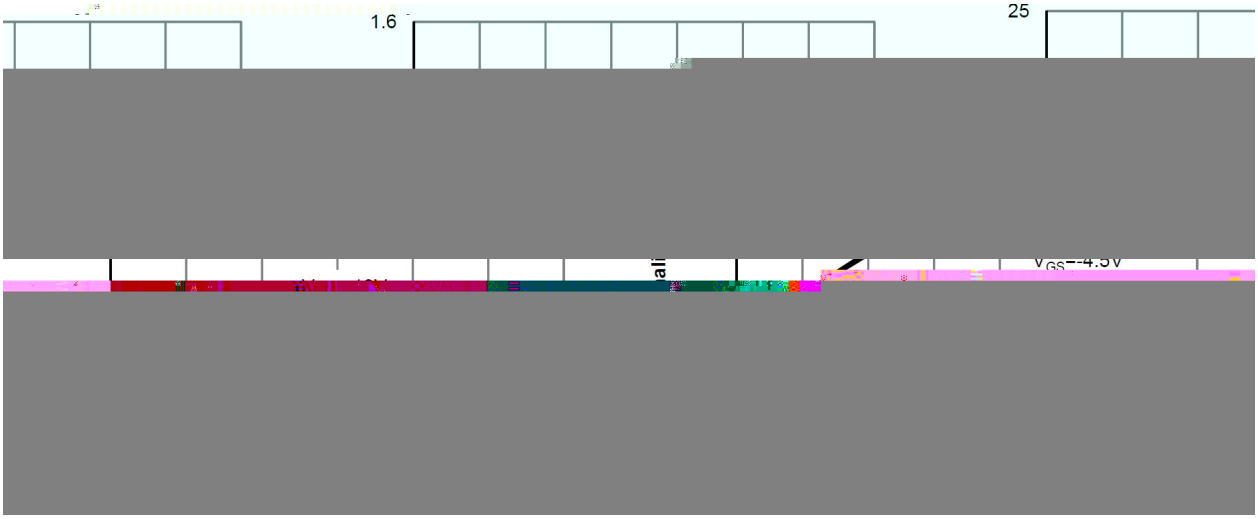
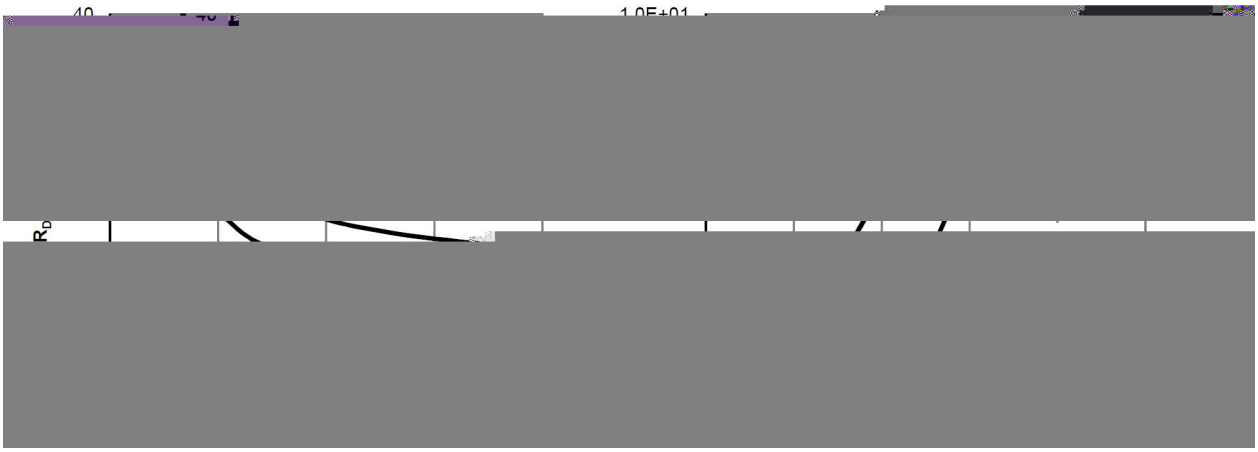
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±25	V
Continuous Drain Current	I_D (T_a=25°C)	-14	A
Pulsed Drain Current	I_{DM}	-56	A
Power Dissipation for Single Operation	P_D (T_a=25℃)	3.1	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Thermal Resistance-

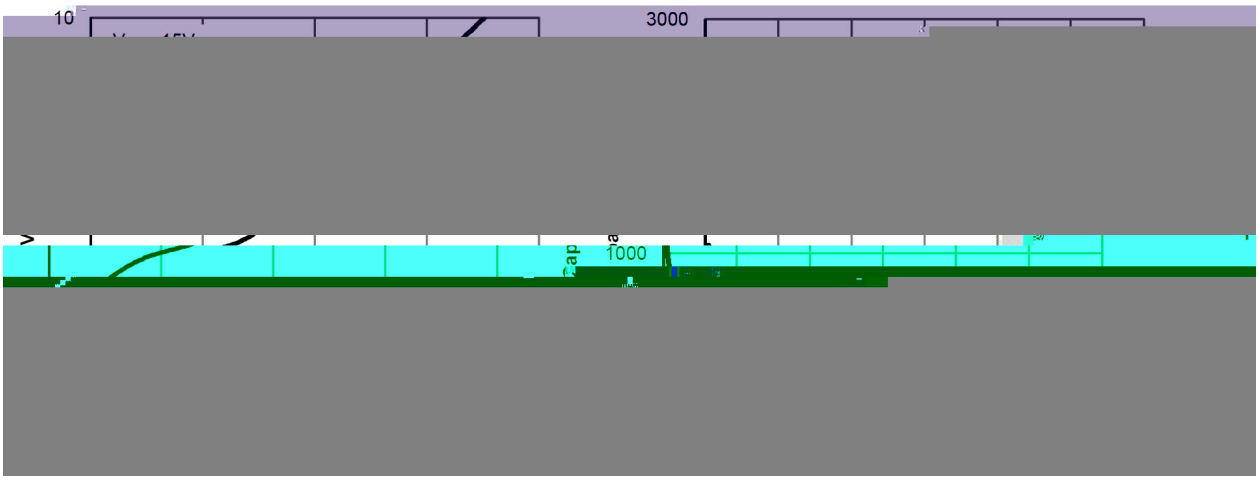
/ Electrical Characteristic Curve

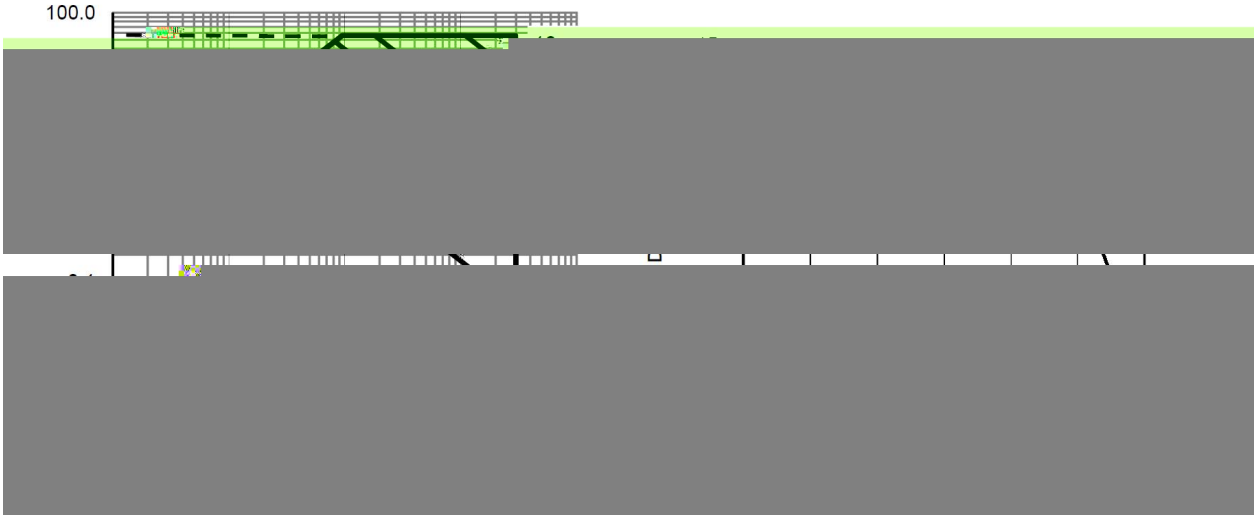


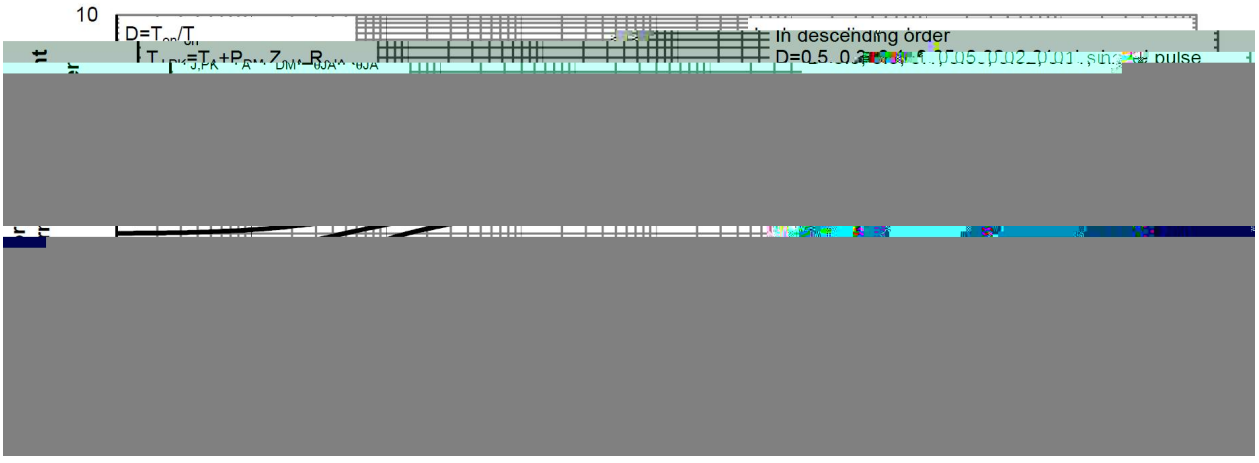




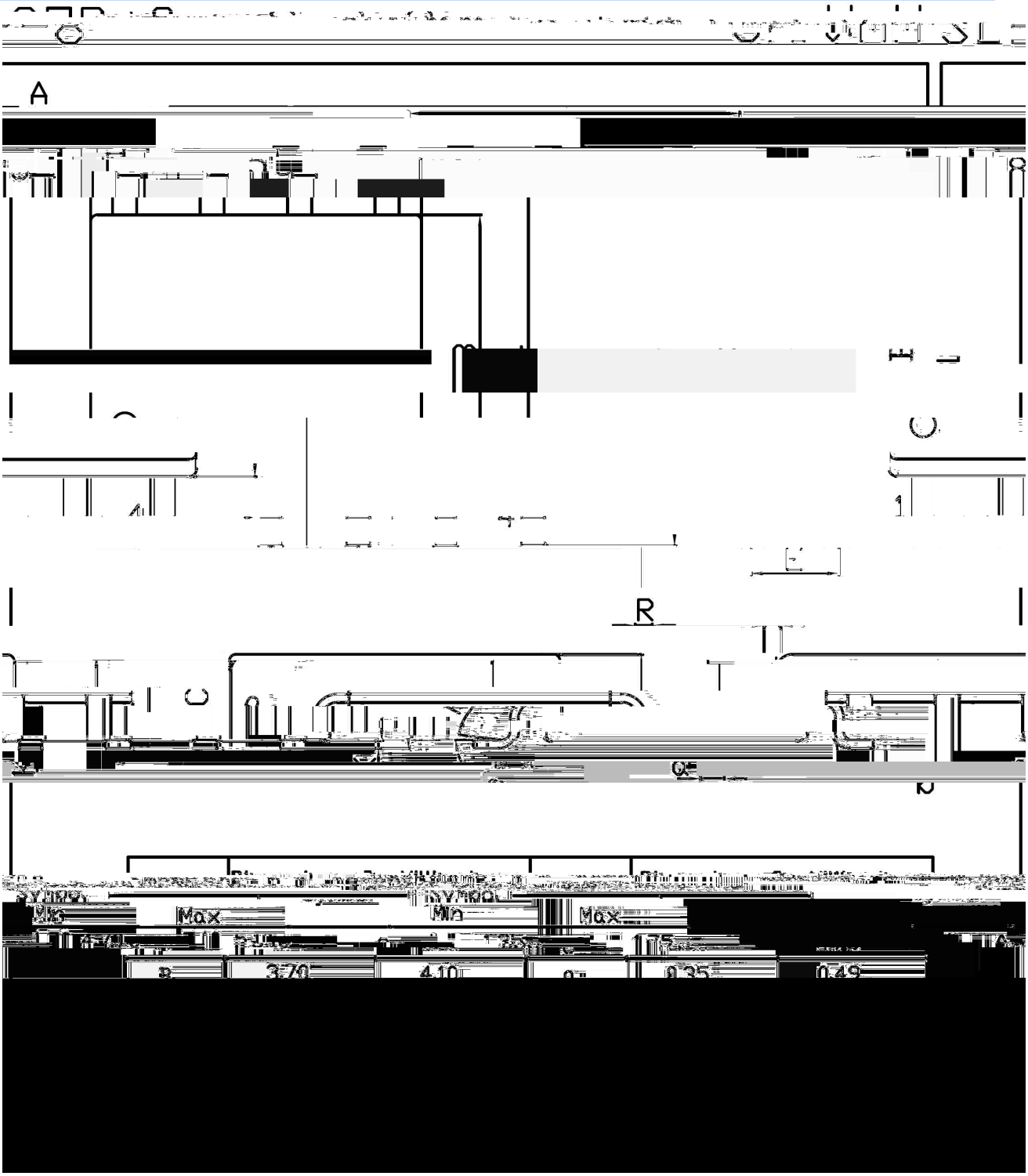
/ Electrical Characteristic Curve



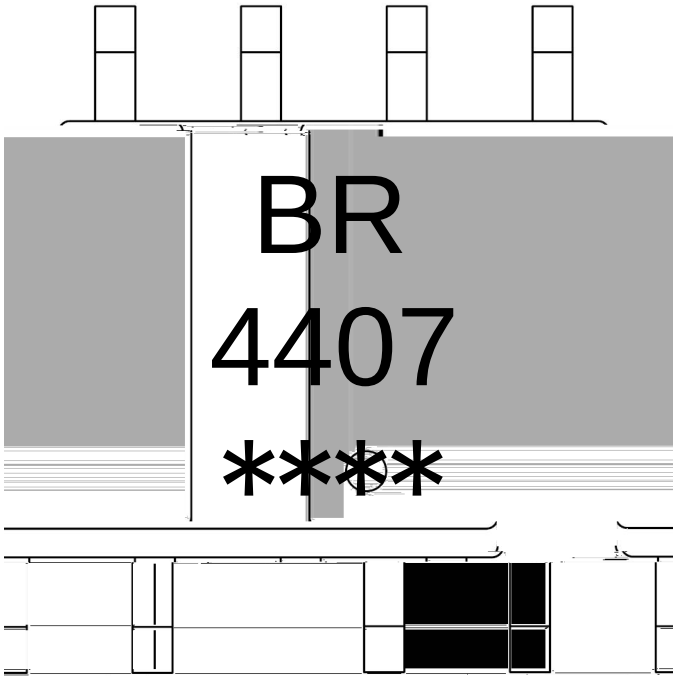




/ Package Dimensions



/ Marking Instructions



BR

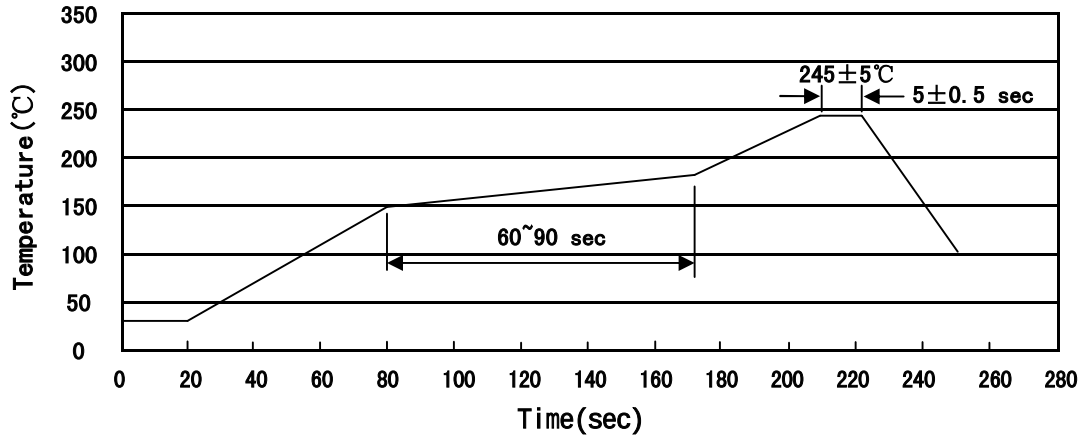
4407

****

Note:

BR:	Company Code
4407:	Product Type
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1		150	180		60	90sec;
2		245±5				5±0.5sec;
3				2		10℃/sec.

1.Preheating:150~180℃, Time:60~90sec.
2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
							盒	箱
						〃		

/ Notices